

2SB861

Silicon PNP Triple Diffused

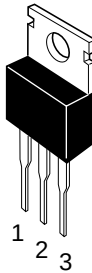
HITACHI

Application

Low frequency power amplifier color TV vertical deflection output complementary pair with 2SD1138

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (T_a = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V _{CBO}	−200	V
Collector to emitter voltage	V _{CEO}	−150	V
Emitter to base voltage	V _{EBO}	−6	V
Collector current	I _C	−2	A
Collector peak current	I _{C(peak)}	−5	A
Collector power dissipation	P _C	1.8	W
	P _C *1	30	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	−45 to +150	°C

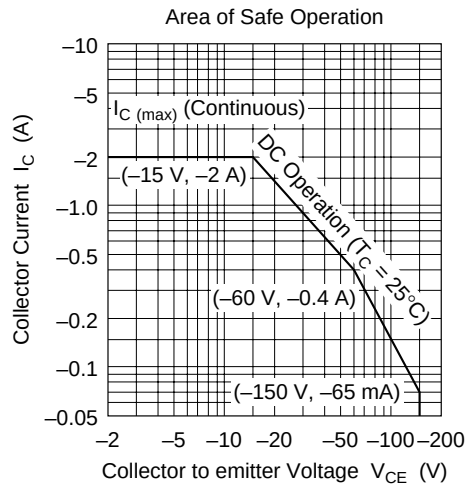
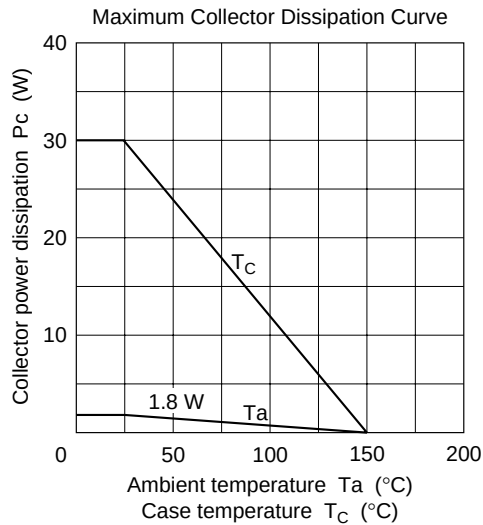
Note: 1. Value at T_C = 25°C

Electrical Characteristics (Ta = 25°C)

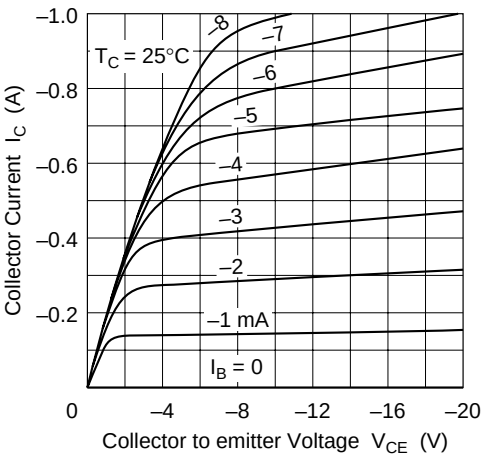
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CBO}$	-150	—	—	V	$I_C = -50\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	—	—	V	$I_E = -5\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1	μA	$V_{CB} = -120\text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200		$V_{CE} = -4\text{ V}$, $I_C = -50\text{ mA}$
	h_{FE2}	60	—	—		$V_{CE} = -10\text{ V}$, $I_C = -500\text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-3	V	$I_C = -500\text{ mA}$, $I_B = -50\text{ mA}$
Base to emitter voltage	V_{BE}	—	—	-1	V	$V_{CE} = -4\text{ V}$, $I_C = -50\text{ mA}$
Collector output capacitance	C_{ob}	—	30	—	pF	$V_{CB} = -100\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$

Notes: 1. The 2SB861 is grouped by h_{FE1} as follows.
2. Pulse test

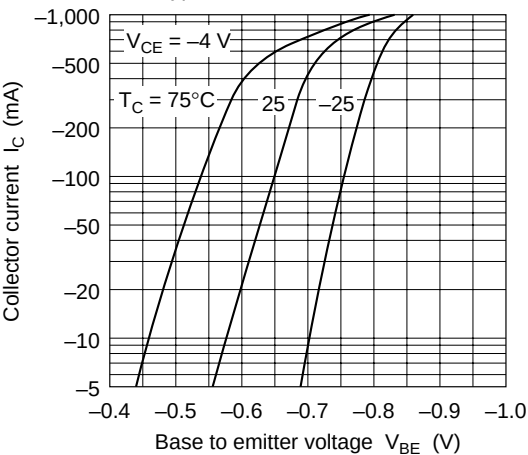
B	C
60 to 120	100 to 200



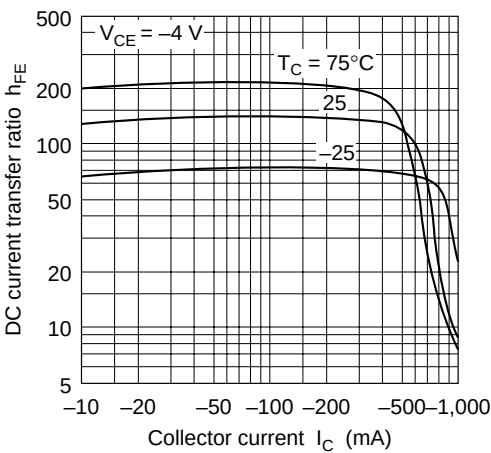
Typical Output Characteristics



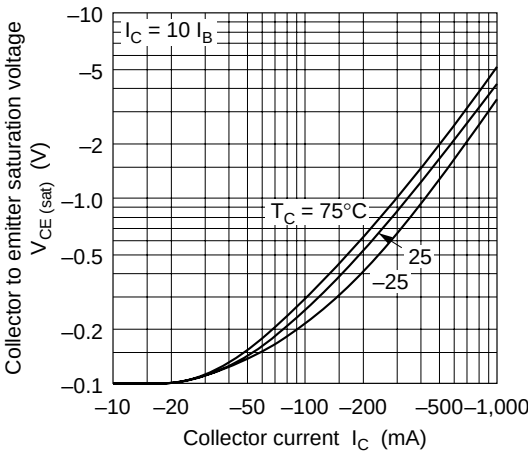
Typical Transfer Characteristics

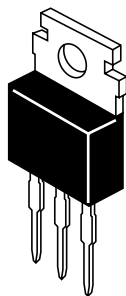
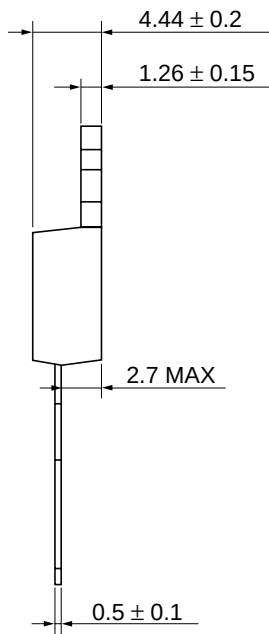
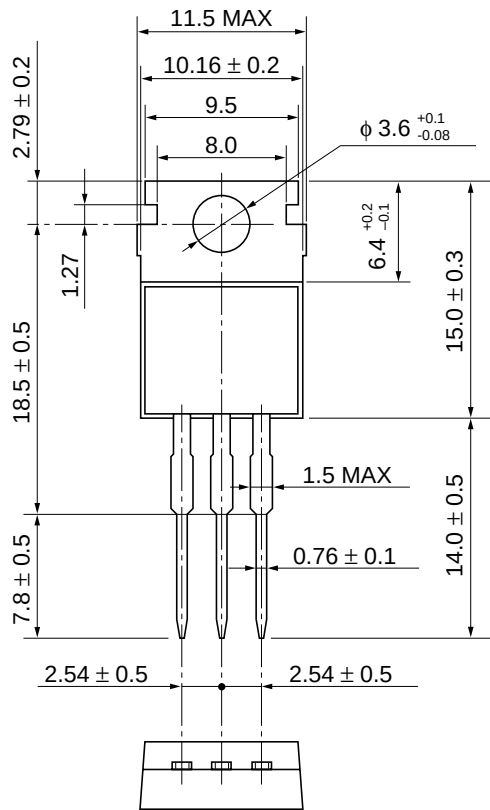


DC Current Transfer Ratio vs. Collector Current



Collector to Emitter Saturation Voltage vs. Collector Current





Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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